



SHEET 1 OF 1

INFORMATION DISCLOSURE
CITATION IN AN
APPLICATION

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U.S. PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
MT		US 6,432,802 B	08/13/2002	NODA et al.	
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FOREIGN PATENT DOCUMENTS

EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes - Number - Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No

OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.
MT		JOHN, S et al.: "Strained Si n-channel metal-oxide-semiconductor transistor on relaxed Si _{1-x} Gex formed by ion implantation of Ge," Applied Physics Letters, American Institute of Physics, April 5, 1999, Vo. 74, No. 14, pp. 2076-2078

EXAMINER
/Michael Trinh/DATE CONSIDERED
06/28/2006

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